

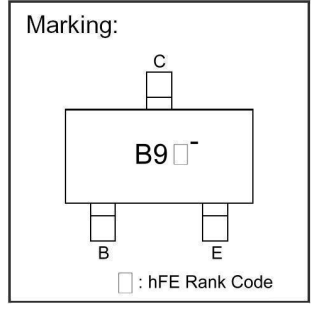
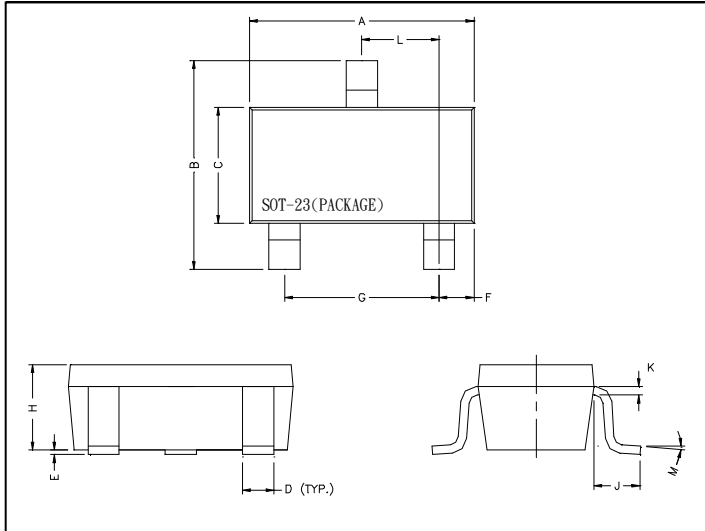
GMBT8550

PNP EPITAXIAL TRANSISTOR

Description

The GMBT8550 is designed for general purpose amplifier applications.

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	-25	V
Collector to Emitter Voltage	VCEO	-20	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	IC	-700	mA
Total Power Dissipation	PD	225	mW

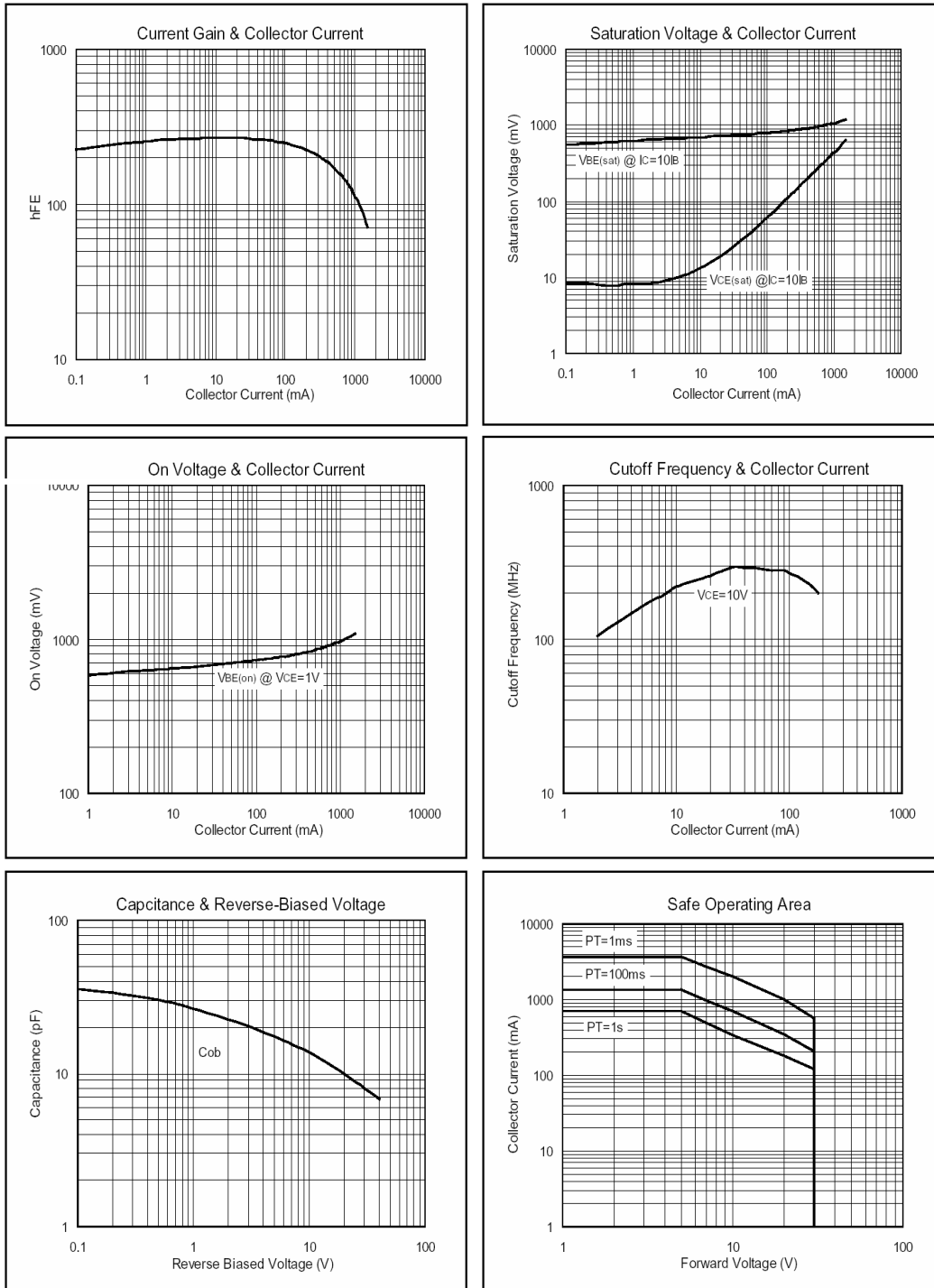
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-25	-	-	V	IC=-10uA
BVCEO	-20	-	-	V	IC=-1mA
BVEBO	-5	-	-	V	IE=-10uA
ICBO	-	-	-1	uA	VCB=-20V
IEBO	-	-	-100	nA	VEB=-6V
VCE(sat)	-	-	-500	mV	IC=-500mA, IB=-50mA
VBE(on)	-	-	-1	V	VCE=-1V, IC=-150mA
hFE	100	-	500		VCE=-1V, IC=-150mA
fT	150	-	-	MHz	VCE=-10V, IC=-20mA, f=100MHz
Cob	-	-	10	pF	VCB=-10V, f=1MHz

Classification Of hFE

Rank	B9C	B9D	B9E
hFE	100 - 200	150 - 300	250 - 500

Characteristics Curve



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